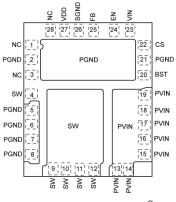
### **Ordering Information**

Р	Part Number	Voltage	Switching Frequency	Junction Temperature Range	Package	Lead Finish
Μ	IIC26950YJL	Adjustable	300kHz	–40°C to +125°C	28-pin 5mm $\times$ 6mm MLF <sup>®</sup>	Pb-Free

## **Pin Configuration**



28-Pin 5mm X 6mm MLF<sup>®</sup> (YJL)

### **Pin Description**

Pin Number	Pin Name	Pin Function	
13,14,15, 16,17,18, 19	PVIN	High-Side N-internal MOSFET Drain Connection (Input): The $PV_{IN}$ operating voltage range is from 4.5V to 26V. Input capacitors between $PV_{IN}$ and the power ground (PGND) are required.	
24	Enable (Input): A logic level control of the output. The EN pin is CMOS-compatible. Logic high or floating = enable, logic low = shutdown. In the off state, supply current of the device is greatly reduct (typically 0.8mA).		
		Feedback (Input): Input to the transconductance amplifier of the control loop. The FB pin is regulated to 0.8V. A resistor divider connecting the feedback to the output is used to adjust the desired output voltage.	
26 SGND Signal ground. SGND must be connected directly to the ground planes. Do the PGND Pad on the top layer.		Signal ground. SGND must be connected directly to the ground planes. Do not route the SGND pin to the PGND Pad on the top layer.	
		$V_{\text{DD}}$ Bias (Input): Power to the internal reference and control sections of the MIC26950. The $V_{\text{DD}}$ operating voltage range is from 4.5V to 5.5V. A 2.2 $\mu\text{F}$ ceramic capacitor from the VDD pin-to-PGND is recommended for clean operation.	
2, 5, 6, 7, 8, 21 PGND		Power Ground. PGND is the ground path for the MIC26950 buck converter power stage. The PGND pin connects to the sources of low-side N-Channel internal MOSFETs, the negative terminals of input capacitors, and the negative terminals of output capacitors. The loop for the power ground should be as small as possible and separate from the Signal ground (SGND) loop.	
22	CS	Current Sense (Input): High current output driver return. The CS pin connects directly to the switch node. Due to the high speed switching on this pin, the CS pin should be routed away from sensitive nodes. CS pin also senses the current by monitoring the voltage across the low-side internal MOSFET during OFF-time.	

## **Pin Description (Continued)**

Pin Number	Pin Name	Pin Function
		Boost (Output): Bootstrapped voltage to the high-side N-channel internal MOSFET driver. A Schottky diode is connected between the VDD pin and the BST pin. A boost capacitor of $0.1\mu$ F is connected between the BST pin and the SW pin.
4, 9, 10, 11, 12       Switch Node (Output): Internal connection for the high-side MOSFET source and low-side Model of the high-side Model of		Switch Node (Output): Internal connection for the high-side MOSFET source and low-side MOSFET drain.
23	23 VIN Power Supply Voltage (Input): Requires bypass capacitor to SGND.	
1, 3, 28	NC	No Connect.

## Absolute Maximum Ratings<sup>(1,2)</sup>

PV <sub>IN</sub> to PGND	0.3V to +28V
V <sub>IN</sub> to PGND	–0.3V to PV <sub>IN</sub>
V <sub>DD</sub> to PGND	–0.3V to +6V
V <sub>SW</sub> , V <sub>CS</sub> to PGND	–0.3V to (PV <sub>IN</sub> +0.3V)
$V_{BST}$ to $V_{SW}$	–0.3V to 6V
V <sub>BST</sub> to PGND	–0.3V to 34V
V <sub>EN</sub> to PGND	–0.3V to (V <sub>DD</sub> + 0.3V)
V <sub>FB</sub> to PGND	
PGND to SGND	–0.3V to +0.3V
Junction Temperature	
Storage Temperature (T <sub>S</sub> )	
Lead Temperature (soldering, 10sec).	260°C

## **Operating Ratings**<sup>(3)</sup>

Supply Voltage (PV <sub>IN</sub> , V <sub>IN</sub> )	4.5V to 26V
Output Voltage Range (V <sub>OUT</sub> )	0.8V to 5.5V
Bias Voltage (V <sub>DD</sub> )	4.5V to 5.5V
Enable Input (V <sub>EN</sub> )	$\cdots$ 0V to V <sub>DD</sub>
Junction Temperature (T <sub>J</sub> )	–40°C to +125°C
Maximum Power Dissipation	Note 4
Package Thermal Resistance <sup>(4)</sup>	
5mm x 6mm $MLF^{\mathbb{B}}(\theta_{JA})$	

## Electrical Characteristics<sup>(5)</sup>

 $PV_{IN} = V_{IN} = 12V, V_{DD} = 5V; V_{BST} - V_{SW} = 5V; T_A = 25^{\circ}C, unless noted.$ **Bold** values indicate  $-40^{\circ}C \le T_J \le +125^{\circ}C.$ 

Parameter	Condition	Min.	Тур.	Max.	Units	
Power Supply Input						
Input Voltage Range (V <sub>IN</sub> , PV <sub>IN</sub> )		4.5		26	V	
V <sub>DD</sub> Bias Voltage						
Operating Bias Voltage (V <sub>DD</sub> )		4.5	5	5.5	V	
Undervoltage Lockout Trip Level	V <sub>DD</sub> Rising	2.4	2.7	3.2	V	
UVLO Hysteresis			50		mV	
Quiescent Supply Current	V <sub>FB</sub> = 1.5V		1.4	3	mA	
Chutdown Cunchy Current	V <sub>DD</sub> = V <sub>BST</sub> = 5.5V, V <sub>IN</sub> = 26V		0.7	2	mA	
Shutdown Supply Current	SW = unconnected, $V_{EN} = 0V$					
Reference		·				
	0°C ≤T <sub>J</sub> ≤ 85°C (±1.0%)	0.792	0.8	0.808	V	
Feedback Reference Voltage	–40°C ≤TJ ≤ 125°C (±1.5%)	0.788	0.8	0.812	V	
Load Regulation	I <sub>OUT</sub> = 0A to 12A		0.2		%	
Line Regulation	V <sub>IN</sub> = (V <sub>OUT</sub> + 3.0V) to 26V		0.1		%	
FB Bias Current	V <sub>FB</sub> = 0.8V		5		nA	
Enable Control	•	·		•	•	
EN Logic Level High	4.5V < V <sub>DD</sub> < 5.5V	1.2	0.85		V	
EN Logic Level Low	4.5V < V <sub>DD</sub> < 5.5V		0.78	0.4	V	
EN Bias Current	$V_{EN} = 0V$		50		μA	

Notes:

1. Exceeding the absolute maximum rating may damage the device.

2. Devices are ESD sensitive. Handling precautions recommended. Human body model,  $1.5k\Omega$  in series with 100pF.

3. The device is not guaranteed to function outside operating range.

4.  $PD_{(MAX)} = (T_{J(MAX)} - T_A)/\theta_{JA}$ , where  $\theta_{JA}$  depends upon the printed circuit layout. See "Applications Information."

5. Specification for packaged product only.

## Electrical Characteristics<sup>(5)</sup>

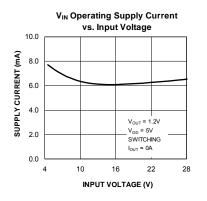
Parameter	Condition	Min.	Тур.	Max.	Units
Oscillator					
Switching Frequency (6)		225	300	375	kHz
Maximum Duty Cycle (7)	V <sub>FB</sub> = 0V		87		%
Minimum Duty Cycle	V <sub>FB</sub> > 0.8V		0		%
Minimum Off-Time			360		ns
Soft-Start			·		
Soft-Start Time			6		ms
Short-Circuit Protection					
Current-Limit Threshold	V <sub>FB</sub> = 0.8V	13.2	27		Α
Short-Circuit Current	V <sub>FB</sub> = 0V		8		А
Internal FETs					
Top-MOSFET R <sub>DS (ON)</sub>	I <sub>SW</sub> = 1A		17		mΩ
Bottom-MOSFET R <sub>DS (ON)</sub>	I <sub>SW</sub> = 1A		6		mΩ
SW Leakage Current	$PV_{IN} = 26V, V_{SW} = 26V, V_{EN} = 0V, V_{BST} = 31.5 V$			60	μA
V <sub>IN</sub> Leakage Current	PV <sub>IN</sub> = 26V, V <sub>SW</sub> = 0V, V <sub>EN</sub> = 0V, V <sub>BST</sub> = 31.5V			25	μA
Thermal Protection	· · · · · · · · · · · · · · · · · · ·		·	-	•
Over-temperature Shutdown	T <sub>J</sub> Rising		155		°C
Over-temperature Shutdown Hysteresis			10		°C

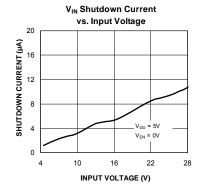
Notes:

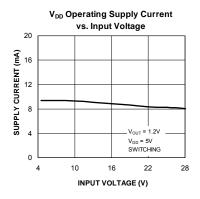
6. Measured in test mode.

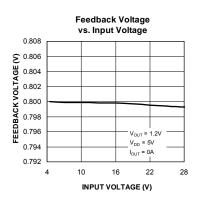
7. The maximum duty-cycle is limited by the fixed mandatory off-time  $t_{\mbox{\scriptsize OFF}}$  of typically 360ns.

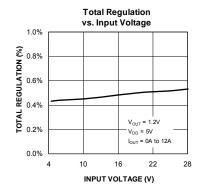
## **Typical Characteristics**

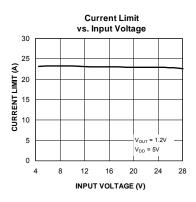


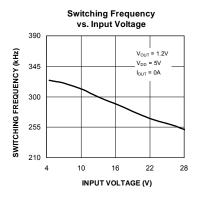












- -

= 12V

70 100 130

70 100 130

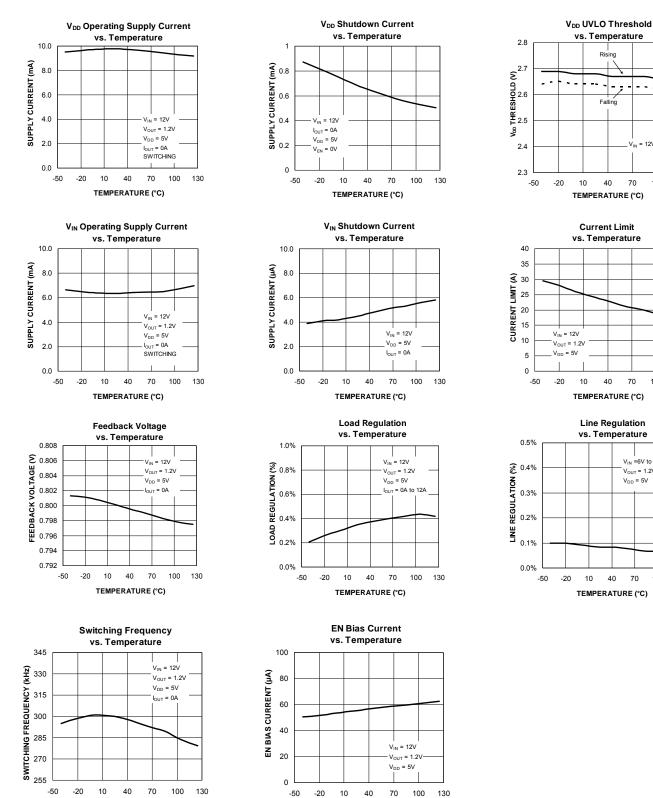
V<sub>IN</sub> =6V to 26V

V<sub>OUT</sub> = 1.2V

V<sub>DD</sub> = 5V

70 100 130

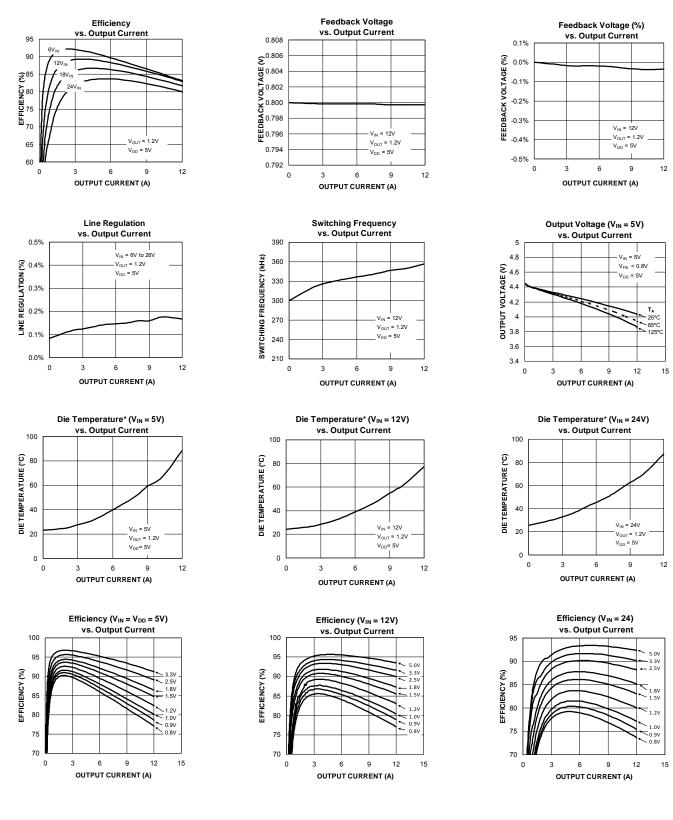
## **Typical Characteristics (Continued)**

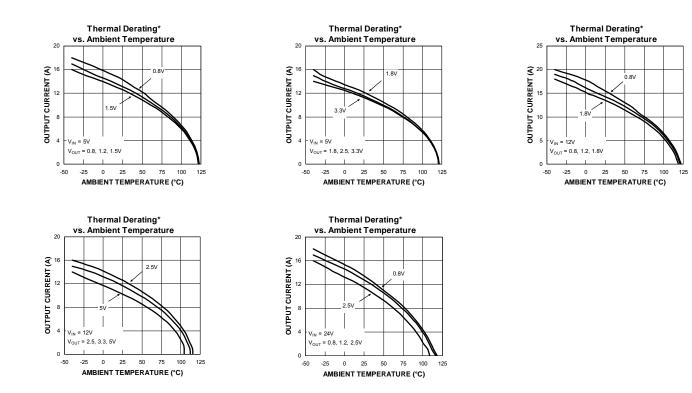


TEMPERATURE (°C)

TEMPERATURE (°C)

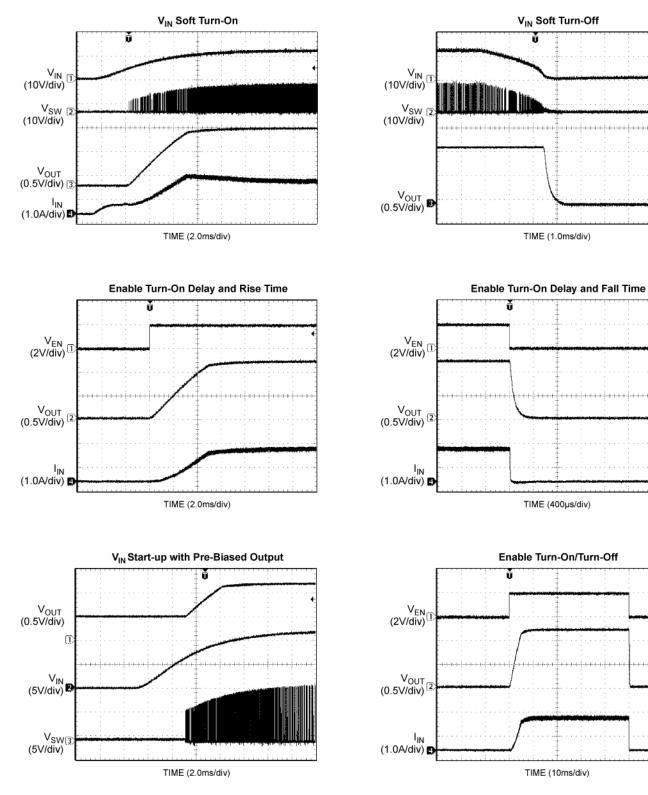
## **Typical Characteristics (Continued)**

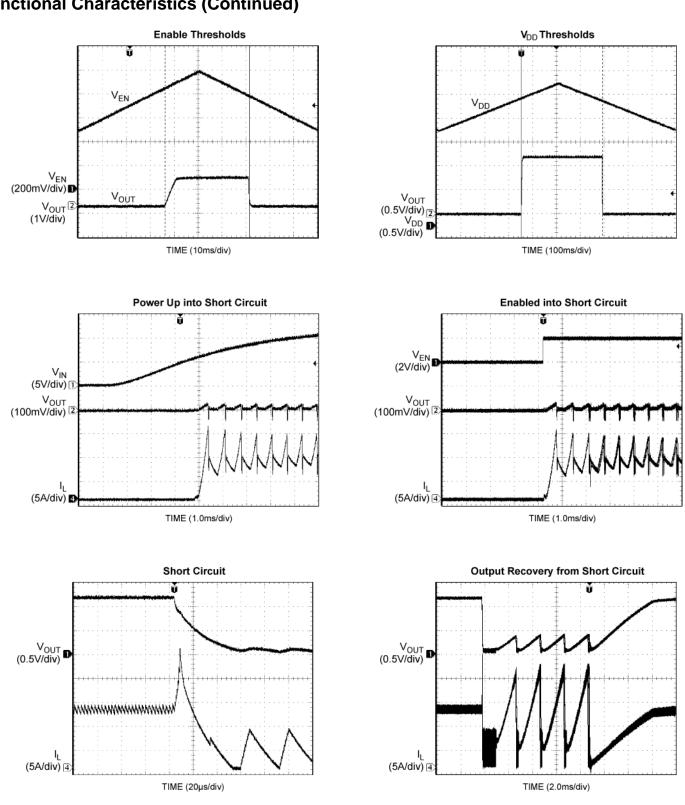




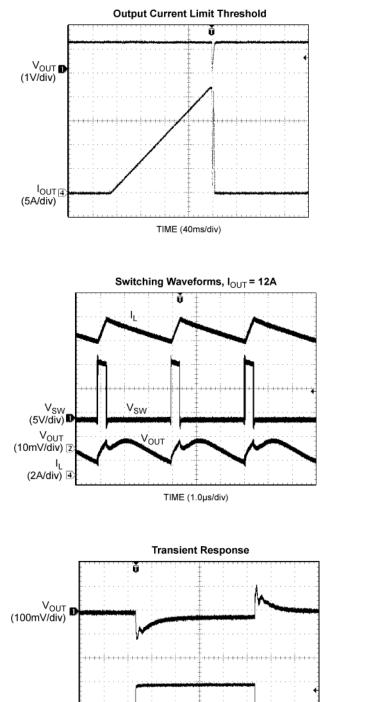
**Die Temperature\*** : The temperature measurement was taken at the hottest point on the MIC26950 case mounted on a 5 square inch 4 layer, 0.62", FR-4 PCB with 2oz finish copper weight per layer, see Thermal Measurement section. Actual results will depend upon the size of the PCB, ambient temperature and proximity to other heat emitting components.

### **Functional Characteristics**



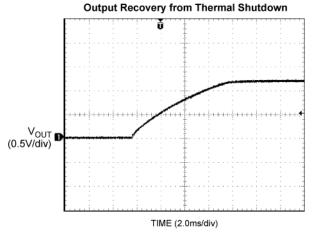


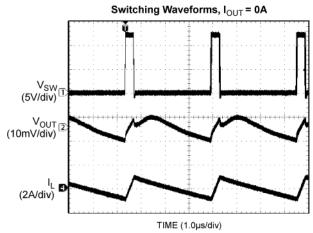
**Functional Characteristics (Continued)** 



TIME (200µs/div)

### **Functional Characteristics (Continued)**





I<sub>OUT</sub> (2) (5A/div)

## **Functional Diagram**

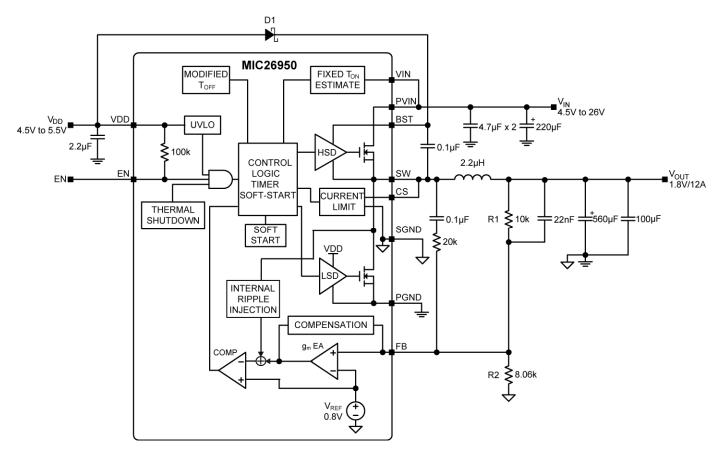


Figure 1. MIC26950 Block Diagram

### **Functional Description**

The MIC26950 is an adaptive ON-time synchronous step-down DC-DC regulator. It is designed to operate over a wide input voltage range from 4.5V to 26V and provides a regulated output voltage at up to 12A of output current. A digitally modified adaptive ON-time control scheme is employed in to obtain a constant switching frequency and to simplify the control compensation. Over-current protection is implemented without the use of an external sense resistor. The device includes an internal soft-start function which reduces the power supply input surge current at start-up by controlling the output voltage rise time.

#### **Theory of Operation**

Figure 1 illustrates the block diagram for the control loop of the MIC26950. The output voltage is sensed by the MIC26950 feedback pin FB via the voltage divider R1 and R2, and compared to a 0.8V reference voltage  $V_{RFF}$ at the error comparator through a low gain transconductance (gm) amplifier. If the feedback voltage decreases and the output of the g<sub>m</sub> amplifier is below 0.8V, then the error comparator will trigger the control logic and generate an ON-time period. The ON-time period length is predetermined by the "FIXED ton ESTIMATION" circuitry:

$$t_{ON(estimated)} = \frac{V_{OUT}}{V_{IN} \times 300 \text{kHz}}$$
(1)

where  $V_{OUT}$  is the output voltage and  $V_{IN}$  is the power stage input voltage.

At the end of the ON-time period, the internal high-side driver turns off the high-side MOSFET and the low-side driver turns on the low-side MOSFET. The OFF-time period length depends upon the feedback voltage in most cases. When the feedback voltage decreases and the output of the  $g_m$  amplifier is below 0.8V, the ON-time period is triggered and the OFF-time period ends. If the OFF-time period determined by the feedback voltage is less than the minimum OFF-time t<sub>OFF(min)</sub>, which is about 360ns, the MIC26950 control logic will apply the t<sub>OFE(min)</sub> instead. t<sub>OFF(min)</sub> is required to maintain enough energy in the boost capacitor  $(C_{BST})$  to drive the high-side MOSFET. The maximum duty cycle is obtained from the 360ns t<sub>OFF(min)</sub>:

$$D_{max} = \frac{t_{S} - t_{OFF(min)}}{t_{S}} = 1 - \frac{360ns}{t_{S}}$$
(2)

where  $t_s = 1/300 \text{kHz} = 3.33 \mu \text{s}$ .

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It is not recommended to use MIC26950 with a OFF-time close to t<sub>OFF(min)</sub> during steady-state operation. Also, as V<sub>OUT</sub> increases, the internal ripple injection will increase and reduce the line regulation performance. Therefore, the maximum output voltage of the MIC26950 should be limited to 5.5V. Please refer to "Setting Output Voltage" subsection in "Application Information" for more details.

The actual ON-time and resulting switching frequency will vary with the part-to-part variation in the rise and fall times of the internal MOSFETs, the output load current, and variations in the VDD voltage. Also, the minimum ton results in a lower switching frequency in high  $V_{IN}$  to  $V_{OUT}$ applications, such as 26V to 1.0V. The minimum  $t_{ON}$ measured on the MIC26950 evaluation board is about 184ns. During load transients, the switching frequency is changed due to the varying OFF-time.

To illustrate the control loop operation, will be analyzed both the steady-state and load transient scenarios. For easy analysis, the gain of the g<sub>m</sub> amplifier is assumed to be 1. With this assumption, the inverting input of the error comparator is the same as the feedback voltage.

Figure 2 shows the MIC26950 control loop timing during steady-state operation. During steady-state, the gm amplifier senses the feedback voltage ripple, which is proportional to the output voltage ripple and the inductor current ripple, to trigger the ON-time period. The ONtime is predetermined by the  $t_{ON}$  estimator. The termination of the OFF-time is controlled by the feedback voltage. At the valley of the feedback voltage ripple, which occurs when  $V_{FR}$  falls below  $V_{RFF}$ , the OFF period ends and the next ON-time period is triggered through the control logic circuitry.

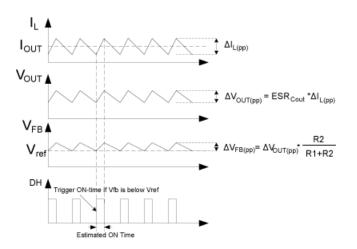


Figure 2. MIC26950 Control Loop Timing

Figure 3 shows the operation of the MIC26950 during a load transient. The output voltage drops due to the sudden load increase, which causes the  $V_{FB}$  to be less than  $V_{REF}$ . This will cause the error comparator to trigger an ON-time period. At the end of the ON-time period, a minimum OFF-time  $t_{OFF(min)}$  is generated to charge  $C_{BST}$  since the feedback voltage is still below  $V_{REF}$ . Then, the next ON-time period is triggered due to the low feedback voltage. Therefore, the switching frequency changes during the load transient, but returns to the nominal fixed frequency once the output has stabilized at the new load current level. With the varying duty cycle and switching frequency, the output recovery time is fast and the output voltage deviation is small in MIC26950 converter.

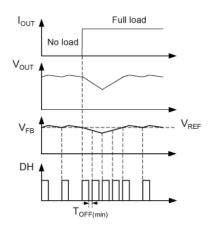


Figure 3. MIC26950 Load Transient Response

Unlike true current-mode control, the MIC26950 uses the output voltage ripple to trigger an ON-time period. The output voltage ripple is proportional to the inductor current ripple if the ESR of the output capacitor is large enough. The MIC26950 control loop has the advantage of eliminating the need for slope compensation.

In order to meet the stability requirements, the MIC26950 feedback voltage ripple should be in phase with the inductor current ripple and large enough to be sensed by the  $g_m$  amplifier and the error comparator. recommended feedback The voltage ripple is 20mV~100mV. If a low ESR output capacitor is selected, the feedback voltage ripple may be too small to be sensed by the g<sub>m</sub> amplifier and the error comparator. Also, the output voltage ripple and the feedback voltage ripple are not necessarily in phase with the inductor current ripple if the ESR of the output capacitor is very low. In these cases, ripple injection is required to ensure proper operation. Please refer to "Ripple Injection" subsection in "Application Information" for more details about the ripple injection technique.

#### Soft-Start

Soft-start reduces the power supply input surge current at startup by controlling the output voltage rise time. The input surge appears while the output capacitor is charged up. A slower output rise time will draw a lower input surge current.

The MIC26950 implements an internal digital soft-start by making the 0.8V reference voltage  $V_{REF}$  ramp from 0 to 100% in about 6ms with a 9.7mV step. Therefore, the output voltage is controlled to increase slowly by a staircase  $V_{FB}$  ramp. Once the soft-start cycle ends, the related circuitry is disabled to reduce current consumption.  $V_{DD}$  must be powered up at the same time or after  $V_{IN}$  to make the soft-start function behavior correctly.

#### **Current Limit**

The MIC26950 uses the  $R_{DS(ON)}$  of the internal low-side power MOSFET to sense over-current conditions. This method will avoid adding cost, board space and power losses taken by a discrete current sense resistor. The low-side MOSFET is used because it displays much lower parasitic oscillations during switching than the high-side MOSFET.

In each switching cycle of the MIC26950 converter, the inductor current is sensed by monitoring the low-side MOSFET in the OFF period. If the inductor current is greater than 27A, then the MIC26950 turns off the high-side MOSFET and a soft-start sequence is triggered. This mode of operation is called "hiccup mode" and its purpose is to protect the downstream load in case of a hard short. The current limit threshold has a fold back characteristic related to the feedback voltage. As shown in Figure 4.

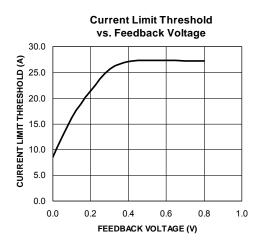


Figure 4. MIC26950 Current Limiting Circuit

#### **MOSFET Gate Drive**

The Block Diagram of Figure 1 shows a bootstrap circuit, consisting of D1 (a Schottky diode is recommended) and  $C_{BST}$ . This circuit supplies energy to the high-side drive circuit. Capacitor  $C_{BST}$  is charged, while the low-side MOSFET is on, and the voltage on the SW pin is approximately 0V. When the high-side MOSFET driver is turned on, energy from  $C_{BST}$  is used to turn the MOSFET on. As the high-side MOSFET turns on, the voltage on the SW pin increases to approximately  $V_{IN}$ . Diode D1 is reversed biased and  $C_{BST}$  floats high while continuing to keep the high-side MOSFET on. The bias current of the high-side driver is less than 10mA so a 0.1µF to 1µF is sufficient to hold the gate voltage with minimal droop for the power stroke (high-side switching) cycle, i.e.  $\Delta BST = 10mA \times 3.33\mu S/0.1\mu F = 333mV$ .

When the low-side MOSFET is turned back on,  $C_{BST}$  is recharged through D1. A small resistor  $R_G$ , which is in series with  $C_{BST}$ , can be used to slow down the turn-on time of the high-side N-channel MOSFET.

The drive voltage is derived from the V<sub>DD</sub> supply voltage. The nominal low-side gate drive voltage is V<sub>DD</sub> and the nominal high-side gate drive voltage is approximately V<sub>DD</sub> – V<sub>DIODE</sub>, where V<sub>DIODE</sub> is the voltage drop across D1. An approximate 30ns delay between the high-side and low-side driver transitions is used to prevent current from simultaneously flowing unimpeded through both MOSFETs.

### **Application Information**

#### **Inductor Selection**

Values for inductance, peak, and RMS currents are required to select the output inductor. The input and output voltages and the inductance value determine the peak-to-peak inductor ripple current. Generally, higher inductance values are used with higher input voltages. Larger peak-to-peak ripple currents will increase the power dissipation in the inductor and MOSFETs. Larger output ripple currents will also require more output capacitance to smooth out the larger ripple current. Smaller peak-to-peak ripple currents require a larger inductance value and therefore a larger and more expensive inductor. A good compromise between size, loss and cost is to set the inductor ripple current to be equal to 20% of the maximum output current. The inductance value is calculated by the Equation 4:

$$L = \frac{V_{OUT} \times (V_{IN(max)} - V_{OUT})}{V_{IN(max)} \times f_{sw} \times 20\% \times I_{OUT(max)}}$$
(4)

where:

 $f_{SW}$  = switching frequency, 300kHz 20% = ratio of AC ripple current to DC output current  $V_{IN(max)}$  = maximum power stage input voltage The peak-to-peak inductor current ripple is:

$$\Delta I_{L(pp)} = \frac{V_{OUT} \times (V_{IN(max)} - V_{OUT})}{V_{IN(max)} \times f_{sw} \times L}$$
(5)

The peak inductor current is equal to the average output current plus one half of the peak-to-peak inductor current ripple.

$$I_{L(pk)} = I_{OUT(max)} + 0.5 \times \Delta I_{L(pp)}$$
(6)

The RMS inductor current is used to calculate the  $I^2R$  losses in the inductor.

$$I_{L(RMS)} = \sqrt{I_{OUT(max)}^{2} + \frac{\Delta I_{L(PP)}^{2}}{12}}$$
 (7)

Maximizing efficiency requires the proper selection of core material and minimizing the winding resistance. The high frequency operation of the MIC26950 requires the use of ferrite materials for all but the most cost sensitive applications. Lower cost iron powder cores may be used but the increase in core loss will reduce the efficiency of the power supply. This is especially noticeable at low output power. The winding resistance decreases efficiency at the higher output current levels. The winding resistance must be minimized although this usually comes at the expense of a larger inductor. The power dissipated in the inductor is equal to the sum of the core and copper losses. At higher output loads, the core losses are usually insignificant and can be ignored. At lower output currents, the core losses can be a significant contributor. Core loss information is usually available from the magnetics vendor. Copper loss in the inductor is calculated by Equation 8:

$$P_{\text{INDUCTOR}(\text{Cu})} = I_{L(\text{RMS})}^{2} \times R_{\text{WINDING}}$$
(8)

The resistance of the copper wire,  $R_{WINDING}$ , increases with the temperature. The value of the winding resistance used should be at the operating temperature.

$$P_{WINDING(Ht)} = R_{WINDING(20^{\circ}C)} \times 1 + 0.0042 \times (T_{H} - T_{20^{\circ}C}))$$
(9)

where:

T<sub>H</sub> = temperature of wire under full load

 $T_{20^{\circ}C}$  = ambient temperature

 $R_{WINDING(20^{\circ}C)}$  = room temperature winding resistance (usually specified by the manufacturer)

#### **Output Capacitor Selection**

The type of the output capacitor is usually determined by its ESR (equivalent series resistance). Voltage and RMS current capability are two other important factors for selecting the output capacitor. Recommended capacitor types are tantalum, low-ESR aluminum electrolytic, OS-CON and POSCAP. The output capacitor's ESR is usually the main cause of the output ripple. The output capacitor ESR also affects the control loop from a stability point of view. The maximum value of ESR is calculated:

$$\mathsf{ESR}_{\mathsf{C}_{\mathsf{OUT}}} \leq \frac{\Delta \mathsf{V}_{\mathsf{OUT}(\mathsf{pp})}}{\Delta \mathsf{I}_{\mathsf{L}(\mathsf{PP})}} \tag{10}$$

where:

 $\Delta V_{OUT(pp)}$  = peak-to-peak output voltage ripple

 $\Delta I_{L(PP)}$  = peak-to-peak inductor current ripple

The total output ripple is a combination of the ESR and output capacitance. The total ripple is calculated in Equation 11:

$$\Delta V_{OUT(pp)} = \sqrt{\left(\frac{\Delta I_{L(PP)}}{C_{OUT} \times f_{SW} \times 8}\right)^{2} + \left(\Delta I_{L(PP)} \times ESR_{C_{OUT}}\right)^{2}}$$
(11)

where:

D = duty cycle

C<sub>OUT</sub> = output capacitance value

#### f<sub>SW</sub> = switching frequency

As described in the "Theory of Operation" subsection in "Functional Description", the MIC26950 requires at least 20mV peak-to-peak ripple at the FB pin to make the g<sub>m</sub> amplifier and the error comparator behave properly. Also, the output voltage ripple should be in phase with the inductor current. Therefore, the output voltage ripple caused by the output capacitors value should be much smaller than the ripple caused by the output capacitor ESR. If low ESR capacitors, such as ceramic capacitors, are selected as the output capacitors, a ripple injection method should be applied to provide the enough feedback voltage ripple. Please refer to the "Ripple Injection" subsection for more details.

The voltage rating of the capacitor should be twice the output voltage for a tantalum and 20% greater for aluminum electrolytic or OS-CON. The output capacitor RMS current is calculated in Equation 12:

$$I_{C_{OUT}(RMS)} = \frac{\Delta I_{L(PP)}}{\sqrt{12}}$$
(12)

The power dissipated in the output capacitor is:

$$P_{\text{DISS}(C_{\text{OUT}})} = I_{C_{\text{OUT}}(\text{RMS})}^{2} \times \text{ESR}_{C_{\text{OUT}}}$$
(13)

#### **Input Capacitor Selection**

The input capacitor for the power stage input  $V_{IN}$  should be selected for ripple current rating and voltage rating. Tantalum input capacitors may fail when subjected to high inrush currents, caused by turning the input supply on. A tantalum input capacitor's voltage rating should be at least two times the maximum input voltage to maximize reliability. Aluminum electrolytic, OS-CON, and multilayer polymer film capacitors can handle the higher inrush currents without voltage de-rating. The input voltage ripple will primarily depend upon the input capacitor's ESR. The peak input current is equal to the peak inductor current, so:

$$\Delta V_{\rm IN} = I_{\rm L(pk)} \times \rm ESR_{\rm CIN}$$
(14)

The input capacitor must be rated for the input current ripple. The RMS value of input capacitor current is determined at the maximum output current. Assuming the peak-to-peak inductor current ripple is low:

$$I_{CIN(RMS)} \approx I_{OUT(max)} \times \sqrt{D \times (1-D)}$$
 (15)

The power dissipated in the input capacitor is:

$$P_{\text{DISS(CIN)}} = I_{\text{CIN(RMS)}}^2 \times \text{ESR}_{\text{CIN}}$$
(16)

#### **Ripple Injection**

The V<sub>FB</sub> ripple required for proper operation of the MIC26950 g<sub>m</sub> amplifier and error comparator is 20mV to 100mV. However, the output voltage ripple is generally designed as 1% to 2% of the output voltage. For a low output voltage, such as a 1V, the output voltage ripple is only 10mV to 20mV, and the feedback voltage ripple is less than 20mV. If the feedback voltage ripple is so small that the g<sub>m</sub> amplifier and error comparator can't sense it, the MIC26950 will lose control and the output voltage is not regulated. In order to have some amount of V<sub>FB</sub> ripple, a ripple injection method is applied for low output voltage ripple applications.

The applications are divided into three situations according to the amount of the feedback voltage ripple:

1) Enough ripple at the feedback voltage due to the large ESR of the output capacitors.

As shown in Figure 5a, the converter is stable without any ripple injection. The feedback voltage ripple is:

$$\Delta V_{FB(pp)} = \frac{R2}{R1 + R2} \times ESR_{C_{OUT}} \times \Delta I_{L(pp)}$$
(17)

where  $\Delta I_{L(pp)}$  is the peak-to-peak value of the inductor current ripple.

2) Inadequate ripple at the feedback voltage due to the small ESR of the output capacitors.

The output voltage ripple is fed into the FB pin through a feedforward capacitor  $C_{\rm ff}$  in this situation, as shown in Figure 5b. The typical  $C_{\rm ff}$  value is between 1nF and 100nF. With the feedforward capacitor, the feedback voltage ripple is very close to the output voltage ripple:

$$\Delta V_{FB(pp)} \approx ESR \times \Delta I_{L(pp)}$$
(18)

3) Virtually no ripple at the FB pin voltage due to the very low ESR of the output capacitors.

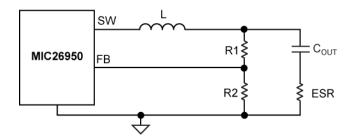


Figure 5a. Enough Ripple at FB

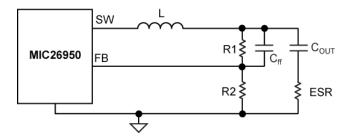


Figure 5b. Inadequate Ripple at FB

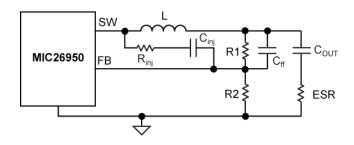


Figure 5c. Invisible Ripple at FB

In this situation, the output voltage ripple is less than 20mV. Therefore, additional ripple is injected into the FB pin from the switching node SW via a resistor  $R_{inj}$  and a capacitor  $C_{inj}$ , as shown in Figure 5c. The injected ripple is:

$$\Delta V_{FB(pp)} = V_{IN} \times K_{div} \times D \times (1 - D) \times \frac{1}{f_{SW} \times \tau}$$
(19)

$$K_{div} = \frac{R1//R2}{R_{ini} + R1//R2}$$
(20)

where

 $V_{IN}$  = Power stage input voltage D = duty cycle  $f_{SW}$  = switching frequency  $\tau$  = (R1//R2//R<sub>inj</sub>) × C<sub>ff</sub>

In equations (19) and (20), it is assumed that the time constant associated with  $C_{\rm ff}$  must be much greater than the switching period:

$$\frac{1}{f_{SW} \times \tau} = \frac{T}{\tau} \ll 1$$
 (21)

If the voltage divider resistors R1 and R2 are in the k $\Omega$  range, a C<sub>ff</sub> of 1nF to 100nF can easily satisfy the large time constant requirements. Also, a 100nF injection capacitor C<sub>inj</sub> is used in order to be considered as short for a wide range of the frequencies.

The process of sizing the ripple injection resistor and capacitors is:

**Step 1.** Select  $C_{\rm ff}$  to feed all output ripples into the feedback pin and make sure the large time constant assumption is satisfied. Typical choice of  $C_{\rm ff}$  is 1nF to 100nF if R1 and R2 are in k $\Omega$  range.

*Step 2.* Select R<sub>inj</sub> according to the expected feedback voltage ripple using Equation 22:

$$K_{div} = \frac{\Delta V_{FB(pp)}}{V_{IN}} \times \frac{f_{SW} \times \tau}{D \times (1 - D)}$$
(22)

Then the value of R<sub>inj</sub> is obtained as:

$$R_{inj} = (R1//R2) \times (\frac{1}{K_{div}} - 1)$$
 (23)

*Step 3.* Select C<sub>inj</sub> as 100nF, which could be considered as short for a wide range of the frequencies.

#### Setting Output Voltage

The MIC26950 requires two resistors to set the output voltage as shown in Figure 6.

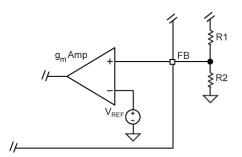


Figure 6. Voltage-Divider Configuration

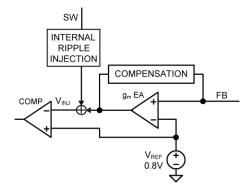
The output voltage is determined by the equation:

$$V_{OUT} = V_{FB} \times (1 + \frac{R1}{R2})$$
(24)

where,  $V_{FB} = 0.8V$ . A typical value of R1 can be between  $3k\Omega$  and  $10k\Omega$ . If R1 is too large, it may allow noise to be introduced into the voltage feedback loop. If R1 is too small, it will decrease the efficiency of the power supply, especially at light loads. Once R1 is selected, R2 can be calculated using:

$$R2 = \frac{V_{FB} \times R1}{V_{OUT} - V_{FB}}$$
(25)

In addition to the external ripple injection added at the FB pin, internal ripple injection is added at the inverting input of the comparator inside the MIC26950, as shown in Figure 7. The inverting input voltage  $V_{\rm INJ}$  is clamped to 1.2V. As  $V_{\rm OUT}$  is increased, the swing of  $V_{\rm INJ}$  will be clamped. The clamped  $V_{\rm INJ}$  reduces the line regulation because it is reflected back as a DC error on the FB terminal. Therefore, the maximum output voltage of the MIC26950 should be limited to 5.5V to avoid this line regulation problem.





#### **Thermal Measurements**

Measuring the IC's case temperature is recommended to ensure it is within its operating limits. Although this might seem like a very elementary task, it is easy to get erroneous results. The most common mistake is to use the standard thermal couple that comes with a thermal meter. This thermal couple wire gauge is large, typically 22 gauge, and behaves like a heatsink, resulting in a lower case measurement.

Two methods of temperature measurement are using a smaller thermal couple wire or an infrared thermometer. If a thermal couple wire is used, it must be constructed of 36 gauge wire or higher (smaller wire size) to minimize the wire heat-sinking effect. In addition, the thermal couple tip must be covered in either thermal grease or thermal glue to make sure that the thermal couple junction is making good contact with the case of the IC. Omega brand thermal couple (5SC-TT-K-36-36) is adequate for most applications.

Wherever possible, an infrared thermometer is recommended. The measurement spot size of most infrared thermometers is too large for an accurate reading on a small form factor ICs. However, a IR thermometer from Optris has a 1mm spot size, which makes it a good choice for measuring the hottest point on the case. An optional stand makes it easy to hold the beam on the IC for long periods of time.

July 2011

### **PCB Layout Guidelines**

# Warning!!! To minimize EMI and output noise, follow these layout recommendations.

PCB Layout is critical to achieve reliable, stable and efficient performance. A ground plane is required to control EMI and minimize the inductance in power, signal and return paths.

The following guidelines should be followed to insure proper operation of the MIC26950 converter.

#### IC

- The  $2.2\mu$ F ceramic capacitor, which is connected to the V<sub>DD</sub> terminal, must be located right at the IC. The V<sub>DD</sub> terminal is very noise sensitive and placement of the capacitor is very critical. Use wide traces to connect to the V<sub>DD</sub> and PGND pins.
- The signal ground pin (SGND) must be connected directly to the ground planes. Do not route the SGND pin to the PGND Pad on the top layer.
- Place the IC close to the point-of-load (POL).
- Use fat traces to route the input and output power lines.
- Signal and power grounds should be kept separate and connected at only one location.

#### **Input Capacitor**

- Place the input capacitor next.
- Place the input capacitors on the same side of the board and as close to the IC as possible.
- Keep both the  $V_{IN}$  Pin and PGND connections short.
- Place several vias to the ground plane close to the input capacitor ground terminal.
- Use either X7R or X5R dielectric input capacitors. Do not use Y5V or Z5U type capacitors.
- Do not replace the ceramic input capacitor with any other type of capacitor. Any type of capacitor can be placed in parallel with the input capacitor.
- If a Tantalum input capacitor is placed in parallel with the input capacitor, it must be recommended for switching regulator applications and the operating voltage must be derated by 50%.
- In "Hot-Plug" applications, a Tantalum or Electrolytic bypass capacitor must be used to limit the over-voltage spike seen on the input supply with power is suddenly applied.

#### Inductor

- Keep the inductor connection to the switch node (SW) short.
- Do not route any digital lines underneath or close to the inductor.
- Keep the switch node (SW) away from the feedback (FB) pin.
- The CS pin should be connected directly to the SW pin to accurate sense the voltage across the low-side MOSFET.
- To minimize noise, place a ground plane underneath the inductor.

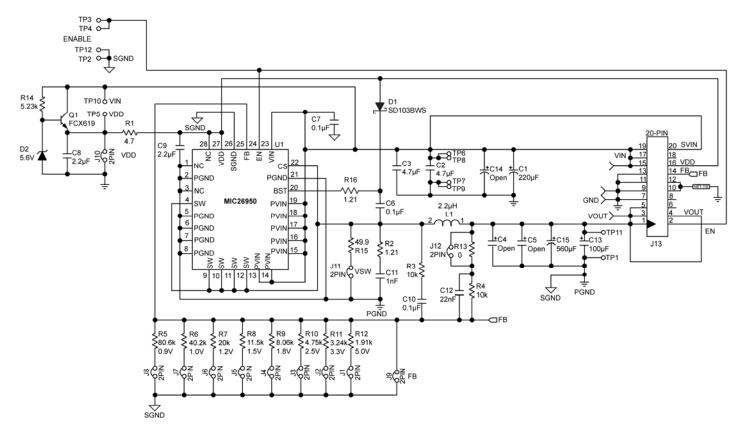
#### **Output Capacitor**

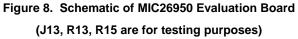
- Use a wide trace to connect the output capacitor ground terminal to the input capacitor ground terminal.
- Phase margin will change as the output capacitor value and ESR changes. Contact the factory if the output capacitor is different from what is shown in the BOM.
- The feedback trace should be separate from the power trace and connected as close as possible to the output capacitor. Sensing a long high current load trace can degrade the DC load regulation.

#### **RC Snubber**

• Place the RC snubber on the same side of the board and as close to the SW pin as possible.

## **Evaluation Board Schematic**





### **Bill of Materials**

ltem	Part Number	Manufacturer	Description	Qty.
C1	B41125A7227M	EPCOS <sup>(1)</sup>	220µF Aluminum Capacitor, SMD, 35V	1
00.00	12105C475KAZ2A	AVX <sup>(2)</sup>		
C2, C3	GRM32ER71H475KA88L	Murata <sup>(3)</sup>	4.7µF Ceramic Capacitor, X7R, Size 1210, 50V	2
C4, C5	Open			
	06035C104KAT2A	AVX <sup>(2)</sup>		
C6, C7, C10	GRM188R71H104KA93D	Murata <sup>(3)</sup>	0.1µF Ceramic Capacitor, X7R, Size 0603, 50V	3
010	C1608X7R1H104K	TDK <sup>(4)</sup>		
	0805ZC225MAT2A	AVX <sup>(2)</sup>		2
C8,C9	GRM21BR71A225KA01L	Murata <sup>(3)</sup>	2.2µF Ceramic Capacitor, X7R, Size 0805, 10V	
	C2012X7R1A225K	TDK <sup>(4)</sup>		
	06035C102KAT2A	AVX <sup>(2)</sup>		
C11	GRM188R71H102KA01D	Murata <sup>(3)</sup>	1nF Ceramic Capacitor, X7R, Size 0603, 50V	1
	C1608X7R1H102K	TDK <sup>(4)</sup>		
	06035C223KAZ2A	AVX <sup>(2)</sup>		
C12	GRM188R71H223K	Murata <sup>(3)</sup>	22nF Ceramic Capacitor, X7R, Size 0603, 50V	1
	C1608X7R1H223K	TDK <sup>(4)</sup>		
040	12106D107MAT2A	AVX <sup>(2)</sup>		
C13	GRM32ER60J107ME20L	Murata <sup>(3)</sup>	100µF Ceramic Capacitor, X5R, Size 1210, 6.3V	1
C14	Open			
C15	6SEPC560MX	SANYO <sup>(5)</sup>	560µF OSCON Capacitor, 6.3V	1
D4	SD103AWS-7	Diodes Inc <sup>(6)</sup>		
D1	SD103AWS	Vishay <sup>(7)</sup>	Small Signal Schottky Diode	1
D2	CMDZ5L6	Central Semi <sup>(8)</sup>	5.6V Zener Diode	1
L1	HCF1305-2R2-R	Cooper Bussmann <sup>(9)</sup>	2.2µH Inductor, 15A Saturation Current	1
Q1	FCX619	ZETEX <sup>(6)</sup>	50V NPN Transistor	1
R1	CRCW06034R75FKEA	Vishay Dale <sup>(7)</sup>	4.75Ω Resistor, Size 0603, 1%	1
R2, R16	CRCW08051R21FKEA	Vishay Dale <sup>(7)</sup>	1.21Ω Resistor, Size 0805, 1%	2
R3, R4	CRCW060310K0FKEA	Vishay Dale <sup>(7)</sup>	10kΩ Resistor, Size 0603, 1%	2

Notes:

1. EPCOS: <u>www.epcos.com</u>.

2. AVX: <u>www.avx.com</u>.

3. Murata: <u>www.murata.com</u>.

4. TDK: <u>www.tdk.com</u>.

5. SANYO: <u>www.sanyo.com</u>.

6. Diode Inc.: <u>www.diodes.com</u>.

7. Vishay: <u>www.vishay.com</u>.

8. Central Semi: <u>www.centralsemi.com</u>.

9. Cooper Bussmann: <u>www.cooperbussmann.com</u>.

10. Micrel, Inc.: <u>www.micrel.com</u>.

## Bill of Materials (Continued)

ltem	Part Number	Manufacturer	Description	Qty.
R5	CRCW060380K6FKEA	Vishay Dale <sup>(7)</sup>	80.6kΩ Resistor, Size 0603, 1%	1
R6	CRCW060340K2FKEA	Vishay Dale <sup>(7)</sup>	40.2kΩ Resistor, Size 0603, 1%	1
R7	CRCW060320K0FKEA	Vishay Dale <sup>(7)</sup>	20kΩ Resistor, Size 0603, 1%	1
R8	CRCW060311K5FKEA	Vishay Dale <sup>(7)</sup>	11.5kΩ Resistor, Size 0603, 1%	1
R9	CRCW06038K06FKEA	Vishay Dale <sup>(7)</sup>	8.06kΩ Resistor, Size 0603, 1%	1
R10	CRCW06034K75FKEA	Vishay Dale <sup>(7)</sup>	4.75kΩ Resistor, Size 0603, 1%	1
R11	CRCW06033K24FKEA	Vishay Dale <sup>(7)</sup>	3.24kΩ Resistor, Size 0603, 1%	1
R12	CRCW06031K91FKEA	Vishay Dale <sup>(7)</sup>	1.91kΩ Resistor, Size 0603, 1%	1
R13	CRCW06030000FKEA	Vishay Dale <sup>(7)</sup>	0Ω Resistor, Size 0603, 5%	1
R14	CRCW06035K23FKEA	Vishay Dale <sup>(7)</sup>	5.23kΩ Resistor, Size 0603, 1%	1
R15	CRCW060349R9FKEA	Vishay Dale <sup>(7)</sup>	49.9Ω Resistor, Size 0603, 1%	1
U1	MIC26950YJL	Micrel. Inc. <sup>(10)</sup>	26V/12A Synchronous Buck DC-DC Regulator	1

## **PCB** Layout

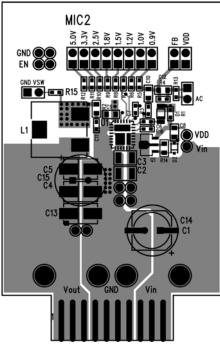


Figure 9. MIC26950 Evaluation Board Top Layer

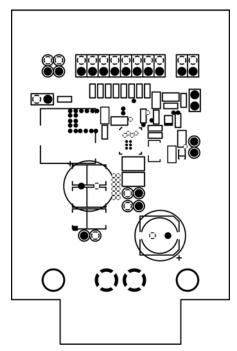


Figure 10. MIC26950 Evaluation Board Mid-Layer 1 (Ground Plane)

## PCB Layout (Continued)

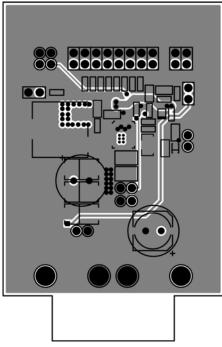


Figure 11. MIC26950 Evaluation Board Mid-Layer 2

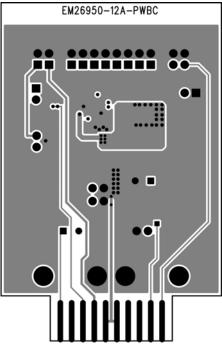
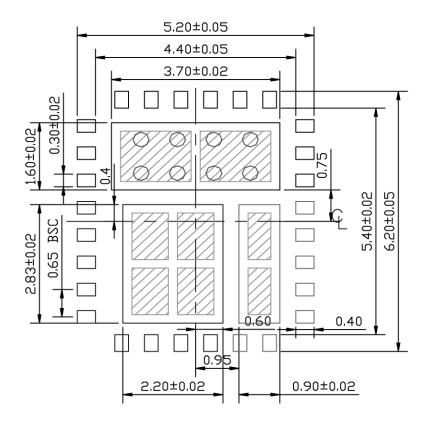
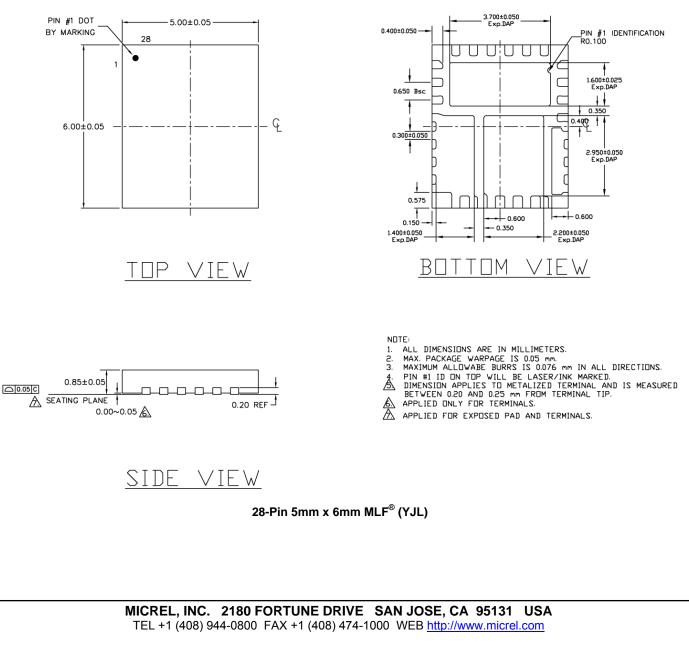


Figure 12. MIC26950 Evaluation Board Bottom Layer

### **Recommended Land Pattern**



### **Package Information**



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